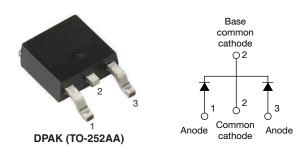
Vishay Semiconductors



Hyperfast Rectifier, 2 x 5 A FRED Pt[®]



PRIMARY CHARACTERISTICS									
I _{F(AV)}	2 x 5 A								
V _R	200 V								
V _F at I _F	0.74 V								
t _{rr} (typ.)	23 ns								
T _J max.	175 °C								
Package	DPAK (TO-252AA)								
Circuit configuration	Common cathode								

FEATURES

- · Hyperfast recovery time
- 175 °C max. operating junction temperature
- · Output rectification freewheeling
- Low forward voltage drop reduced Q_{rr} and soft RoHS recovery COMPLIANT HALOGEN
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS											
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS							
Peak repetitive reverse voltage	V _{RRM}		200	V							
Average rectified forward current	I _{F(AV)}	T _C = 160 °C	10	٨							
Non-repetitive peak surge current	I _{FSM}	$T_{\rm J} = 25 \ ^{\circ}{\rm C}$	80	A							
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C							

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-					
Forward voltage		I _F = 5 A	-	0.90	0.98	.,				
	V _F	I _F = 10 A - 0.9				V				
		I _F = 5 A, T _J = 150 °C	-	0.74	0.84	,				
		I _F = 10 A, T _J = 150 °C	-	0.84	1.05					
		$V_{\rm R} = V_{\rm R}$ rated	-	-	4					
Reverse leakage current per leg	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	40	μA				
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	80					
Junction capacitance per leg	CT	V _R = 600 V	-	17	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH				

Revision: 05-Jun-2023 Document Number: 93263 1 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000



FREE

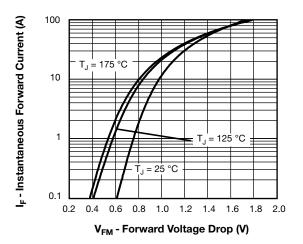


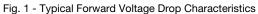
www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)											
PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN.	TYP.	MAX.	UNITS				
		I _F = 1 A, dI _F /dt =	= 100 A/µs, V _R = 30 V	-	23	27					
Reverse recovery time	t _{rr}	T _J = 25 °C		-	21	-	ns				
		T _J = 125 °C		-	26	-					
Peak recovery current	I _{RRM}	T _J = 25 °C	$I_F = 5 A$	-	2	-	А				
		T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 160 V	-	3.1	-	~				
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	20	-	nC				
neverse recovery charge	Qrr	T _J = 125 °C		-	41	-	no				

THERMAL - MECHANICAL SPECIFICATIONS											
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range		T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, junction to case	per leg	R _{thJC}		-	2.7	3.2	°C/W				
	per device			-	1.35	1.6					
Approximate weight					0.3		g				
					0.01		oz.				
Marking device			Case style DPAK (TO-252AA)	10CWH02FN							





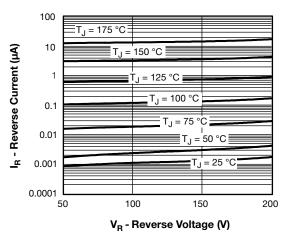


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

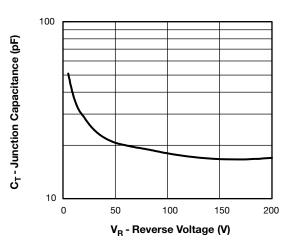


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

 Revision: 05-Jun-2023
 2
 Document Number: 93263

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

www.vishay.com 10 Z_{thJC} - Thermal Impedance (°C/W) D = 0.5D = 02 1 D = 0.1D D = 0.02Single Pulse D = 0.01(Thermal Resistance) 0.1 1E-04 1E-03 1E-02 1E-05 1E-01 1E+00 t₁ - Rectangular Pulse Duration (s)

Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

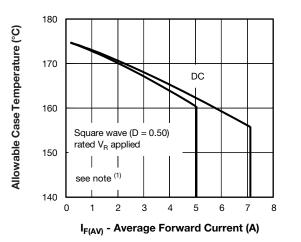
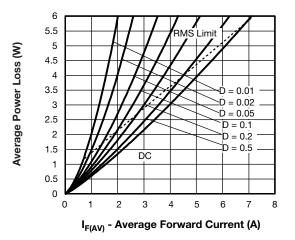
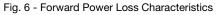


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

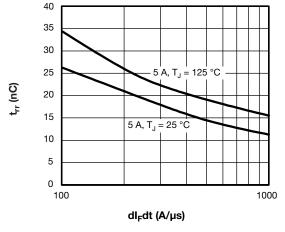


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

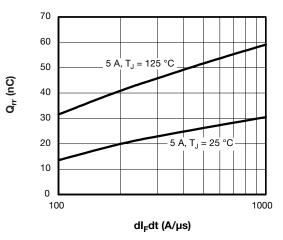


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Document Number: 93263

Revision: 05-Jun-2023 3 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

Vishay Semiconductors



Vis

Vishay Semiconductors



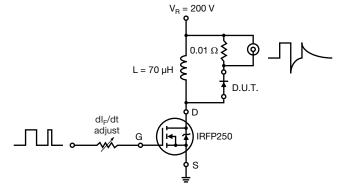


Fig. 9 - Reverse Recovery Parameter Test Circuit

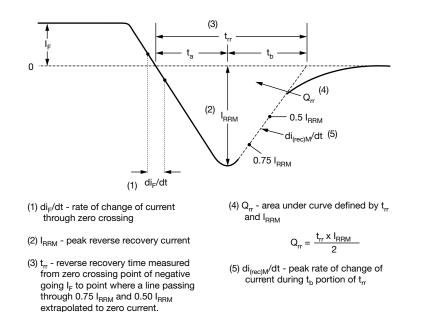


Fig. 10 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors



www.vishay.com

Device code	VS-	10	с	w	ы	02	EN	TRL	-M3
Device code	v3-	10	C	vv	Н	02	FN	IKL	-1413
		2	3	4	5	6	7	8	9
	1	- Visl	nay Sen	nicondu	ctors pro	oduct			
	2	- Cur	rent rati	ng (10 =	= 10 A)				
	3	- Circ	cuit conf	iguratio	n:				
		C =	commo	on catho	de				
	4	- Pac	kage id	entifier:					
		VV =	D-PAK	ζ.					
	Ľ	- H=	hyperfa	ast recov	/ery				
	6 7	- Volt	tage rati	ing (02 =	= 200 V))			
	7	- FN	= TO-28	52AA					
	8	• N	one = tu	ıbe					
		• TI	R = tape	e and re	el				
		• TI	RL = tap	be and r	eel (left	orienteo	d)		
		• TI	RR = ta _l	pe and r	eel (righ	nt orient	ed)		
	9	- Env	rironmer	ntal digit	:				
		-M3	s = halog	gen-free	, RoHS-	-complia	ant and	termina	tions le

ORDERING INFORMATION (Example)										
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION								
VS-10CWH02FN-M3	75	Antistatic plastic tube								
VS-10CWH02FNTR-M3	2000	13" diameter reel								
VS-10CWH02FNTRL-M3	3000	13" diameter reel								
VS-10CWH02FNTRR-M3	3000	13" diameter reel								

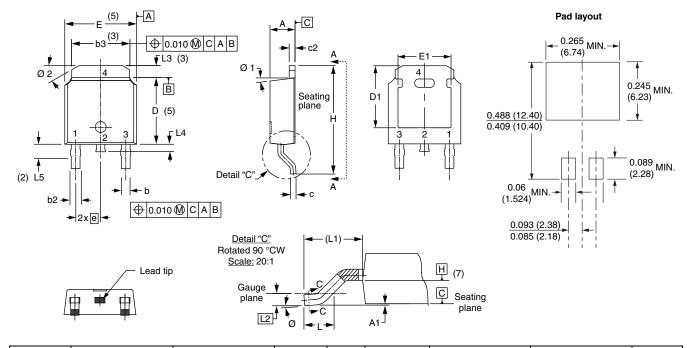
LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95627							
Part marking information	www.vishay.com/doc?95176							
Packaging information	www.vishay.com/doc?95033							
SPICE model	www.vishay.com/doc?95376							





D-PAK (TO-252AA) "M"

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090) BSC	
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	BREF.	
b3	4.95	5.46	0.195	0.215	3		L2	0.51 BSC		0.020 BSC		
С	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁶⁾ Dimension b1 and c1 applied to base metal only

⁽⁷⁾ Datum A and B to be determined at datum plane H

⁽⁸⁾ Outline conforms to JEDEC[®] outline TO-252AA



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.